72Mb M-die DDRII SRAM Specification

165 FBGA with Pb & Pb-Free
(RoHS compliant)

SAMSUNG
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Aug. 2005
Rev 1.0

Document Title

2Mx36-bit, 4Mx18-bit DDR II SIO b2 SRAM

Revision History

Rev. No.	History	Draft Date	Remark
0.0	1. Initial document.	Mar. 9, 2003	Advance
0.1	1. Correct the JTAG ID register definition 2. Correct the AC timing parameter (delete the tKH$\overline{K}$H Max value)	Mar. 20, 2003	Preliminary
0.2	1. Add the Power-on Sequence specification	Aug. 16, 2004	Preliminary
0.3	1. Correct the pin name table	Oct. 18, 2004	Preliminary
0.4	1. Update the power consumption (Icc & Isb)	May. 17, 2005	Preliminary
1.0	1. Finalize the datasheet	Aug. 2, 2005	Final

## 2Mx36-bit, 4Mx18-bit DDR II SIO b2 SRAM

FEATURES

- 1.8V+0.1V/-0.1V Power Supply.
- DLL circuitry for wide output data valid window and future frequency scaling.
- I/O Supply Voltage 1.5V+0.1V/-0.1V for 1.5V I/O, 1.8V+0.1V/-0.1V for 1.8V I/O.
- Separate independent read and write data ports
- HSTL I/O
- Synchronous pipeline read with self timed late write.
- Registered address, control and data input/output.
- Full data coherency, providing most current data.
- DDR(Double Data Rate) Interface on read and write ports.
- Fixed 2-bit burst for both read and write operation.
- Clock-stop supports to reduce current.
- Two input clocks(K and $\overline{K}$) for accurate DDR timing at clock rising edges only.
- Two input clocks for output data(C and $\overline{C}$) to minimize clock-skew and flight-time mismatches.
- Two echo clocks (CQ and $\overline{CQ}$) to enhance output data traceability.
- Single address bus.
- Byte write function.
- Simple depth expansion with no data contention.
- Programmable output impedance.
- JTAG 1149.1 compatible test access port.
- 165FBGA(11x15 ball aray FBGA) with body size of 15x17mm & Lead Free

Org.	Part Number	Cycle Time	Access Time	Unit
X36	K7J643682M-F(E)C(I)30	3.3	0.45	ns
	K7J643682M-F(E)C(I)25	4.0	0.45	ns
	K7J643682M-F(E)C(I)20	5.0	0.45	ns
	K7J643682M-F(E)C(I)16	6.0	0.50	ns
X18	K7J641882M-F(E)C(I)30	3.3	0.45	ns
	K7J641882M-F(E)C(I)25	4.0	0.45	ns
	K7J641882M-F(E)C(I)20	5.0	0.45	ns
	K7J641882M-F(E)C(I)16	6.0	0.50	ns

* E : Lead Free Package

* I : Industrial Temperature

FUNCTIONAL BLOCK DIAGRAM
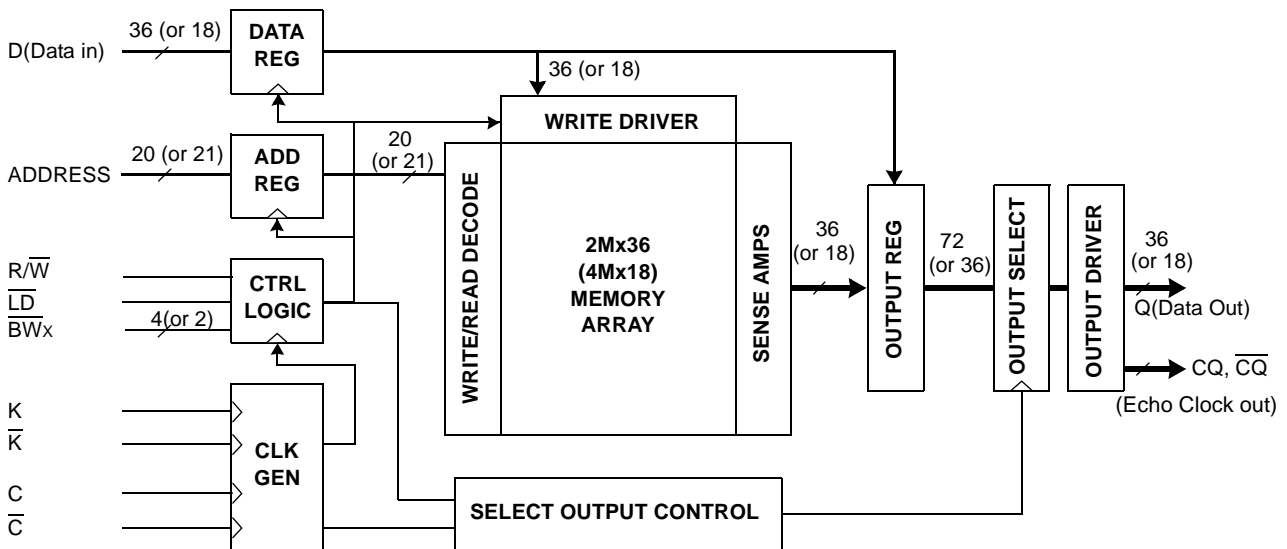
Notes: 1. Numbers in ( ) are for x18 device.

DDR II SRAM and Double Data Rate II comprise a new family of products developed by Cypress, Renesas, IDT, NEC and Samsung technology.

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K7J643682M
K7J641882M
2Mx36 & 4Mx18 DDR II SIO b2 SRAM

PIN CONFIGURATIONS (TOP VIEW)   K7J643682M(2Mx36)

	1	2	3	4	5	6	7	8	9	10	11
A	$\overline{CQ}$	Vss/SA*	SA	R/$\overline{W}$	$\overline{BW_2}$	$\overline{K}$	$\overline{BW_1}$	$\overline{LD}$	SA	Vss/SA*	CQ
B	Q27	Q18	D18	SA	$\overline{BW_3}$	K	$\overline{BW_0}$	SA	D17	Q17	Q8
C	D27	Q28	D19	Vss	SA	SA	SA	Vss	D16	Q7	D8
D	D28	D20	Q19	Vss	Vss	Vss	Vss	Vss	Q16	D15	D7
E	Q29	D29	Q20	VDDQ	Vss	Vss	Vss	VDDQ	Q15	D6	Q6
F	Q30	Q21	D21	VDDQ	VDD	Vss	VDD	VDDQ	D14	Q14	Q5
G	D30	D22	Q22	VDDQ	VDD	Vss	VDD	VDDQ	Q13	D13	D5
H	$\overline{Doff}$	VREF	VDDQ	VDDQ	VDD	Vss	VDD	VDDQ	VDDQ	VREF	ZQ
J	D31	Q31	D23	VDDQ	VDD	Vss	VDD	VDDQ	D12	Q4	D4
K	Q32	D32	Q23	VDDQ	VDD	Vss	VDD	VDDQ	Q12	D3	Q3
L	Q33	Q24	D24	VDDQ	Vss	Vss	Vss	VDDQ	D11	Q11	Q2
M	D33	Q34	D25	Vss	Vss	Vss	Vss	Vss	D10	Q1	D2
N	D34	D26	Q25	Vss	SA	SA	SA	Vss	Q10	D9	D1
P	Q35	D35	Q26	SA	SA	C	SA	SA	Q9	D0	Q0
R	TDO	TCK	SA	SA	SA	$\overline{C}$	SA	SA	SA	TMS	TDI

Notes : 1. * Checked No Connect(NC) pins are reserved for higher density address, i.e. 10A for 144Mb and 2A for 288Mb.

2. $\overline{BW_0}$ controls write to D0:D8, $\overline{BW_1}$ controls write to D9:D17, $\overline{BW_2}$ controls write to D18:D26 and $\overline{BW_3}$ controls write to D27:D35.

PIN NAME

SYMBOL	PIN NUMBERS	DESCRIPTION	NOTE
K, $\overline{K}$	6B, 6A	Input Clock	
C, $\overline{C}$	6P, 6R	Input Clock for Output Data	1
CQ, $\overline{CQ}$	11A, 1A	Output Echo Clock	
$\overline{Doff}$	1H	DLL Disable when low	
SA	3A,9A,4B,8B,5C-7C,5N-7N,4P,5P,7P,8P,3R-5R,7R-9R	Address Inputs	
D0-35	10P,11N,11M,10K,11J,11G,10E,11D,11C,10N,9M,9L 9J,10G,9F,10D,9C,9B,3B,3C,2D,3F,2G,3J,3L,3M,2N 1C,1D,2E,1G,1J,2K,1M,1N,2P	Data Inputs	
Q0-35	11P,10M,11L,11K,10J,11F,11E,10C,11B,9P,9N,10L 9K,9G,10F,9E,9D,10B,2B,3D,3E,2F,3G,3K,2L,3N 3P,1B,2C,1E,1F,2J,1K,1L,2M,1P	Data Outputs	
R/$\overline{W}$	4A	Read, Write Control Pin, Read active when high	
$\overline{LD}$	8A	Synchronous Load Pin, bus Cycle sequence is to be defined when low	
$\overline{BW_0},\overline{BW_1},\overline{BW_2},\overline{BW_3}$	7B,7A,5A,5B	Block Write Control Pin,active when low	
VREF	2H,10H	Input Reference Voltage	
ZQ	11H	Output Driver Impedance Control Input	2
VDD	5F,7F,5G,7G,5H,7H,5J,7J,5K,7K	Power Supply (1.8 V)	
VDDQ	4E,8E,4F,8F,4G,8G,3H,4H,8H,9H,4J,8J,4K,8K,4L,8L	Output Power Supply (1.5V or 1.8V)	
Vss	2A,10A,4C,8C,4D-8D,5E-7E,6F,6G,6H,6J,6K,5L-7L,4M, 8M,4N,8N	Ground	
TMS	10R	JTAG Test Mode Select	
TDI	11R	JTAG Test Data Input	
TCK	2R	JTAG Test Clock	
TDO	1R	JTAG Test Data Output	
NC	-	No Connect	3

Notes: 1. C, $\overline{C}$, K or $\overline{K}$ cannot be set to VREF voltage.

2. When ZQ pin is directly connected to VDD output impedance is set to minimum value and it cannot be connected to ground or left unconnected.

3. Not connected to chip pad internally.

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K7J643682M
K7J641882M

2Mx36 & 4Mx18 DDR II SIO b2 SRAM

PIN CONFIGURATIONS(TOP VIEW) K7J641882M(4Mx18)

	1	2	3	4	5	6	7	8	9	10	11
A	$\overline{CQ}$	Vss/SA*	SA	R/$\overline{W}$	$\overline{BW_1}$	$\overline{K}$	NC	$\overline{LD}$	SA	SA	CQ
B	NC	Q9	D9	SA	NC	K	$\overline{BW_0}$	SA	NC	NC	Q8
C	NC	NC	D10	Vss	SA	SA	SA	Vss	NC	Q7	D8
D	NC	D11	Q10	Vss	Vss	Vss	Vss	Vss	NC	NC	D7
E	NC	NC	Q11	VDDQ	Vss	Vss	Vss	VDDQ	NC	D6	Q6
F	NC	Q12	D12	VDDQ	VDD	Vss	VDD	VDDQ	NC	NC	Q5
G	NC	D13	Q13	VDDQ	VDD	Vss	VDD	VDDQ	NC	NC	D5
H	$\overline{Doff}$	VREF	VDDQ	VDDQ	VDD	Vss	VDD	VDDQ	VDDQ	VREF	ZQ
J	NC	NC	D14	VDDQ	VDD	Vss	VDD	VDDQ	NC	Q4	D4
K	NC	NC	Q14	VDDQ	VDD	Vss	VDD	VDDQ	NC	D3	Q3
L	NC	Q15	D15	VDDQ	Vss	Vss	Vss	VDDQ	NC	NC	Q2
M	NC	NC	D16	Vss	Vss	Vss	Vss	Vss	NC	Q1	D2
N	NC	D17	Q16	Vss	SA	SA	SA	Vss	NC	NC	D1
P	NC	NC	Q17	SA	SA	C	SA	SA	NC	D0	Q0
R	TDO	TCK	SA	SA	SA	$\overline{C}$	SA	SA	SA	TMS	TDI

Notes: 1. * Checked No Connect(NC) pins are reserved for higher density address, i.e. 2A for 144Mb.
2. $\overline{BW_0}$ controls write to D0:D8 and $\overline{BW_1}$ controls write to D9:D17.

PIN NAME

SYMBOL	PIN NUMBERS	DESCRIPTION	NOTE
K, $\overline{K}$	6B, 6A	Input Clock	
C, $\overline{C}$	6P, 6R	Input Clock for Output Data	1
CQ, $\overline{CQ}$	11A, 1A	Output Echo Clock	
$\overline{Doff}$	1H	DLL Disable when low	
SA	3A,9A,10A,4B,8B,5C-7C,5N-7N,4P,5P,7P,8P,3R-5R,7R-9R	Address Inputs	
D0-17	10P,11N,11M,10K,11J,11G,10E,11D,11C,3B,3C,2D, 3F,2G,3J,3L,3M,2N	Data Inputs	
Q0-17	11P,10M,11L,11K,10J,11F,11E,10C,11B,2B,3D,3E, 2F,3G,3K,2L,3N,3P	Data Outputs	
R/$\overline{W}$	4A	Read, Write Control Pin, Read active when high	
$\overline{LD}$	8A	Synchronous Load Pin, bus Cycle sequence is to be defined when low	
$\overline{BW_0}$, $\overline{BW_1}$	7B, 5A	Block Write Control Pin,active when low	
VREF	2H,10H	Input Reference Voltage	
ZQ	11H	Output Driver Impedance Control Input	2
VDD	5F,7F,5G,7G,5H,7H,5J,7J,5K,7K	Power Supply (1.8 V)	
VDDQ	4E,8E,4F,8F,4G,8G,3H,4H,8H,9H,4J,8J,4K,8K,4L,8L	Output Power Supply (1.5V or 1.8V)	
Vss	2A,10A,4C,8C,4D-8D,5E-7E,6F,6G,6H,6J,6K,5L-7L,4M-8M,4N,8N	Ground	
TMS	10R	JTAG Test Mode Select	
TDI	11R	JTAG Test Data Input	
TCK	2R	JTAG Test Clock	
TDO	1R	JTAG Test Data Output	
NC	7A,1B,5B,9B,10B,1C,2C,9C,1D,9D,10D,1E,2E,9E,1F,9F, 10F,1G,9G,10G,1J,2J,9J,1K,2K,9K,1L,9L,10L,1M,2M, 9M,1N,9N,10N,1P,2P,9P	No Connect	3

Notes: 1. C, $\overline{C}$, K or $\overline{K}$ cannot be set to VREF voltage.
2. When ZQ pin is directly connected to VDD output impedance is set to minimum value and it cannot be connected to ground or left unconnected.
3. Not connected to chip pad internally.

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GENERAL DESCRIPTION

The K7J643682M and K7J641882M are 75,497,472-bits DDR Separate I/O Synchronous Pipelined Burst SRAMs.

They are organized as 2,097,152 words by 36bits for K7J643682M and 4,194,304 words by 18 bits for K7J641882M.

The DDR SIO operation is possible by supporting DDR read and write operations through separate data output and input ports.

Memory bandwidth is higher than DDR sram without separate input output as separate read
and write ports eliminate bus turn around cycle.

Address, data inputs, and all control signals are synchronized to the input clock (K or $\overline{K}$).

Normally data outputs are synchronized to output clocks (C and $\overline{C}$), but when C and $\overline{C}$ are tied high,
the data outputs are synchronized to the input clocks (K and $\overline{K}$).

Read data are referenced to echo clock (CQ or $\overline{CQ}$) outputs.

Read address and write address are registered on rising edges of the input K clocks.

Common address bus is used to access address both for read and write operations.

The internal burst counter is fiexd to 2-bit sequential for both read and write operations.

Synchronous pipeline read and late write enable high speed operations.

Simple depth expansion is accomplished by using $\overline{LD}$ for port selection.

Byte write operation is supported with $\overline{BW_0}$ and $\overline{BW_1}$ ($\overline{BW_2}$ and $\overline{BW_3}$) pins for x18 (x36) device.

IEEE 1149.1 serial boundary scan (JTAG) simplifies monitoriing package pads attachment status with system.

The K7J643682M and K7J641882M are implemented with SAMSUNG's high performance 6T CMOS technology
and is available in 165pin FBGA packages. Multiple power and ground pins minimize ground bounce.

Read Operations

Read cycles are initiated by initiating R/$\overline{W}$ as high at the rising edge of the positive input clock K.

Address is presented and stored in the read address register synchronized with K clock.

For 2-bit burst DDR operation, it will access two 36-bit or 18-bit data words with each read command.

The first pipelined data is transfered out of the device triggered by $\overline{C}$ clock following next $\overline{K}$ clock rising edge.

Next burst data is triggered by the rising edge of following C clock rising edge.

Continuous read operations are initated with K clock rising edge.

And pipelined data are transferred out of device on every rising edge of both C and $\overline{C}$ clocks.

In case C and $\overline{C}$ tied to high, output data are triggered by K and $\overline{K}$ insted of C and $\overline{C}$.

When the $\overline{LD}$ is disabled after a read operation, the K7J643682M and K7J641882M will first complete
burst read operation before entering into deselect mode at the next K clock rising edge.

Then output drivers disabled automatically to high impedance state.

Write Operations

Write cycles are initiated by activating R/$\overline{W}$ as low at the rising edge of the positive input clock K.

Address is presented and stored in the write address register synchronized with next K clock.

For 2-bit burst DDR operation, it will write two 36-bit or 18-bit data words with each write command.

The first "late writed" data is transfered and registered in to the device synchronous with next K clock rising edge.

Next burst data is transfered and registered synchronous with following $\overline{K}$ clock rising edge.

Continuous write operations are initated with K rising edge.

And "late writed" data is presented to the device on every rising edge of both K and $\overline{K}$ clocks.

When the $\overline{LD}$ is disabled, the K7J643682M and K7J641882M will enter into deselect mode.

The device disregards input data presented on the same cycle $\overline{W}$ disabled.

The K7J643682M and K7J641882M support byte write operations.

With activating $\overline{BW_0}$ or $\overline{BW_1}$ ($\overline{BW_2}$ or $\overline{BW_3}$) in write cycle, only one byte of input data is presented.

In K7J641882M, $\overline{BW_0}$ controls write operation to D0:D8, $\overline{BW_1}$ controls write operation to D9:D17.

And in K7J643682M $\overline{BW_2}$ controls write operation to D18:D26, $\overline{BW_3}$ controls write operation to D27:D35.

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Single Clock Mode

K7J643682M and K7J641882M can be operated with the single clock pair K and $\overline{K}$, insted of C or $\overline{C}$ for output clocks.
To operate these devices in single clock mode, C and $\overline{C}$ must be tied high during power up
and must be maintained high during operation.
After power up, this device can't change to or from single clock mode.
System flight time and clock skew could not be compensated in this mode.

Depth Expansion

Separate input and output ports enables easy depth expansion.
Each port can be selected and deselected independently and read and write operation do not affect each other.
Before chip deselected, all read and write pending operations are completed.

Programmable Impedance Output Buffer Operation

The designer can program the SRAM's output buffer impedance by terminating the ZQ pin to V_{SS} through a precision resistor(RQ).
The value of RQ (within 15%) is five times the output impedance desired.
For example, 250Ω resistor will give an output impedance of 50Ω.
Impedance updates occur early in cycles that do not activate the outputs, such as deselect cycles.
In all cases impedance updates are transparent to the user and do not produce access time "push-outs" or other anomalous
behavior in the SRAM.
There are no power up requirements for the SRAM. However, to guarantee optimum output driver impedance after power up, the
SRAM needs 1024 non-read cycles.

Echo clock operation

To assure the output tracibility, the SRAM provides the output Echo clock, pair of compliment clock CQ and $\overline{CQ}$,
which are synchronized with internal data output.
Echo clocks run free during normal operation.
The Echo clock is triggered by internal output clock signal, and transfered to external through same structures as output driver.

Clock Consideration

K7J643682M and K7J641882M utlizes internal DLL(Delay-Locked Loops) for maximum output data valid window.
It can be placed into a stopped-clock state to minimize power with a modest restart time of 1024 clock cycles.
Circuitry automatically resets the DLL when absence of input clock is detected.

Power-Up/Power-Down Supply Voltage Sequencing

The following power-up supply voltage application is recommended: V_{SS}, V_{DD}, V_{DDQ}, V_{REF}, then V_{IN}. V_{DD} and V_{DDQ} can be applied
simultaneously, as long as V_{DDQ} does not exceed V_{DD} by more than 0.5V during power-up. The following power-down supply voltage
removal sequence is recommended: V_{IN}, V_{REF}, V_{DDQ}, V_{DD}, V_{SS}. V_{DD} and V_{DDQ} can be removed simultaneously, as long as V_{DDQ}
does not exceed V_{DD} by more than 0.5V during power-down.

K7J643682M
K7J641882M
2Mx36 & 4Mx18 DDR II SIO b2 SRAM

TRUTH TABLES
SYNCHRONOUS TRUTH TABLE

K	$\overline{LD}$	R/$\overline{W}$	D		Q		OPERATION
			D(A0)	D(A1)	Q(A0)	Q(A1)	
Stopped	X	X	Previous state	Previous state	Previous state	Previous state	Clock Stop
↑	H	X	X	X	High-Z	High-Z	No Operation
↑	L	H	X	X	Dout at $\overline{C}$(t+1)	Dout at C(t+2)	Read
↑	L	L	Din at K(t+1)	Din at $\overline{K}$(t+1)	High-Z	High-Z	Write

Notes: 1. X means "Don't Care".

2. The rising edge of clock is symbolized by (↑).

3. Before enter into clock stop status, all pending read and write operations will be completed.

WRITE TRUTH TABLE(x18)

K	$\overline{K}$	$\overline{BW_0}$	$\overline{BW_1}$	OPERATION
↑		L	L	WRITE ALL BYTEs (K↑)
	↑	L	L	WRITE ALL BYTEs ($\overline{K}$↑)
↑		L	H	WRITE BYTE 0 (K↑)
	↑	L	H	WRITE BYTE 0 ($\overline{K}$↑)
↑		H	L	WRITE BYTE 1 (K↑)
	↑	H	L	WRITE BYTE 1 ($\overline{K}$↑)
↑		H	H	WRITE NOTHING (K↑)
	↑	H	H	WRITE NOTHING ($\overline{K}$↑)

Notes: 1. X means "Don't Care".

2. All inputs in this table must meet setup and hold time around the rising edge of input clock K or $\overline{K}$ (↑).

3. Assumes a WRITE cycle was initiated.

4. This table illustates operation for x18 devices.

WRITE TRUTH TABLE(x36)

K	$\overline{K}$	$\overline{BW_0}$	$\overline{BW_1}$	$\overline{BW_2}$	$\overline{BW_3}$	OPERATION
↑		L	L	L	L	WRITE ALL BYTEs (K↑)
	↑	L	L	L	L	WRITE ALL BYTEs ($\overline{K}$↑)
↑		L	H	H	H	WRITE BYTE 0 (K↑)
	↑	L	H	H	H	WRITE BYTE 0 ($\overline{K}$↑)
↑		H	L	H	H	WRITE BYTE 1 (K↑)
	↑	H	L	H	H	WRITE BYTE 1 ($\overline{K}$↑)
↑		H	H	L	L	WRITE BYTE 2 and BYTE 3 (K↑)
	↑	H	H	L	L	WRITE BYTE 2 and BYTE 3 ($\overline{K}$↑)
↑		H	H	H	H	WRITE NOTHING (K↑)
	↑	H	H	H	H	WRITE NOTHING ($\overline{K}$↑)

Notes: 1. X means "Don't Care".

2. All inputs in this table must meet setup and hold time around the rising edge of input clock K or $\overline{K}$ (↑).

3. Assumes a WRITE cycle was initiated.

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ABSOLUTE MAXIMUM RATINGS*

PARAMETER	SYMBOL	RATING	UNIT
Voltage on V_{DD} Supply Relative to V_{SS}	V_{DD}	-0.5 to 2.9	V
Voltage on V_{DDQ} Supply Relative to V_{SS}	V_{DDQ}	-0.5 to V_{DD}	V
Voltage on Input Pin Relative to V_{SS}	V_{IN}	-0.5 to V_{DD}+0.3	V
Storage Temperature	T_{STG}	-65 to 150	°C
Operating Temperature (Commercial / Industrial)	T_{OPR}	0 to 70 / -40 to 85	°C
Storage Temperature Range Under Bias	T_{BIAS}	-10 to 85	°C

*Note: 1. Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operating sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

2. V_{DDQ} must not exceed V_{DD} during normal operation.

OPERATING CONDITIONS (0°C ≤ T_A ≤ 70°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT
Supply Voltage	V_{DD}	1.7	1.9	V
	V_{DDQ}	1.4	1.9	V
Reference Voltage	V_{REF}	0.68	0.95	V

DC ELECTRICAL CHARACTERISTICS (V_{DD}=1.8V ±0.1V, T_A=0°C to +70°C)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	MAX	UNIT	NOTES
Input Leakage Current	I_{IL}	V_{DD}=Max ; V_{IN}=V_{SS} to V_{DDQ}		-2	+2	µA	
Output Leakage Current	I_{OL}	Output Disabled,		-2	+2	µA	
Operating Current (x36): QDR mode	I_{CC}	V_{DD}=Max , I_{OUT}=0mA Cycle Time ≥ t_{KHKH} Min	-30	-	900	mA	1,4
			-25	-	800		
			-20	-	700		
			-16		650		
Operating Current (x18): QDR mode	I_{CC}	V_{DD}=Max , I_{OUT}=0mA Cycle Time ≥ t_{KHKH} Min	-30	-	850	mA	1,4
			-25	-	750		
			-20	-	650		
			-16	-	600		
Standby Current(NOP): QDR mode	I_{SB1}	Device deselected, I_{OUT}=0mA, f=Max, All Inputs≤0.2V or ≥ V_{DD}-0.2V	-30	-	400	mA	1,5
			-25	-	380		
			-20	-	360		
			-16	-	340		
Output High Voltage	V_{OH1}			V_{DDQ}/2-0.12	V_{DDQ}/2+0.12	V	2,6
Output Low Voltage	V_{OL1}			V_{DDQ}/2-0.12	V_{DDQ}/2+0.12	V	2,6
Output High Voltage	V_{OH2}	I_{OH}=-1.0mA		V_{DDQ}-0.2	V_{DDQ}	V	3
Output Low Voltage	V_{OL2}	I_{OL}=1.0mA		V_{SS}	0.2	V	3
Input Low Voltage	V_{IL}			-0.3	V_{REF}-0.1	V	7,8
Input High Voltage	V_{IH}			V_{REF}+0.1	V_{DDQ}+0.3	V	7,9

Notes: 1. Minimum cycle. I_{OUT}=0mA.
2. $|I_{OH}|$=(V_{DDQ}/2)/(RQ/5)±15% for 175Ω ≤ RQ ≤ 350Ω. $|I_{OL}|$=(V_{DDQ}/2)/(RQ/5)±15% for 175Ω ≤ RQ ≤ 350Ω.
3. Minimum Impedance Mode when ZQ pin is connected to V_{DDQ}.
4. Operating current is calculated with 50% read cycles and 50% write cycles.
5. Standby Current is only after all pending read and write burst opeactions are completed.
6. Programmable Impedance Mode.
7. These are DC test criteria. DC design criteria is V_{REF}±50mV. The AC V_{IH}/V_{IL} levels are defined separately for measuring timing parameters.
8. V_{IL} (Min)DC=-0.3V, V_{IL} (Min)AC=-1.5V(pulse width ≤ 3ns).
9. V_{IH} (Max)DC=V_{DDQ}+0.3, V_{IH} (Max)AC=V_{DDQ}+0.85V(pulse width ≤ 3ns).

K7J643682M
K7J641882M
2Mx36 & 4Mx18 DDR II SIO b2 SRAM

AC ELECTRICAL CHARACTERISTICS (VDD=1.8V ±0.1V, TA=0°C to +70°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	NOTES
Input High Voltage	VIH (AC)	VREF + 0.2	-	V	1,2
Input Low Voltage	VIL (AC)	-	VREF - 0.2	V	1,2

Notes: 1. This condition is for AC function test only, not for AC parameter test.
    2. To maintain a valid level, the transitioning edge of the input must :
        a) Sustain a constant slew rate from the current AC level through the target AC level, $V_{IL(AC)}$ or $V_{IH(AC)}$
        b) Reach at least the target AC level
        c) After the AC target level is reached, continue to maintain at least the target DC level, $V_{IL(DC)}$ or $V_{IH(DC)}$

AC TIMING CHARACTERISTICS (VDD=1.8V±0.1V, TA=0°C to +70°C)

PARAMETER	SYMBOL	-30 MIN	-30 MAX	-25 MIN	-25 MAX	-20 MIN	-20 MAX	-16 MIN	-16 MAX	UNIT	NOTE
Clock											
Clock Cycle Time (K, $\overline{K}$, C, $\overline{C}$)	tKHKH	3.30	5.25	4.00	6.30	5.00	7.88	6.00	8.40	ns	
Clock Phase Jitter (K, $\overline{K}$, C, $\overline{C}$)	tKC var		0.20		0.20		0.20		0.20	ns	5
Clock High Time (K, $\overline{K}$, C, $\overline{C}$)	tKHKL	1.32		1.60		2.00		2.40		ns	
Clock Low Time (K, $\overline{K}$, C, $\overline{C}$)	tKLKH	1.32		1.60		2.00		2.40		ns	
Clock to $\overline{Clock}$ (K↑→$\overline{K}$↑, C↑→$\overline{C}$↑)	tKH$\overline{K}$H	1.49		1.80		2.20		2.70		ns	
Clock to data clock (K↑→C↑, $\overline{K}$↑→$\overline{C}$↑)	tKHCH	0.00	1.45	0.00	1.80	0.00	2.30	0.00	2.80	ns	
DLL Lock Time (K, C)	tKC lock	1024		1024		1024		1024		cycle	6
K Static to DLL reset	tKC reset	30		30		30		30		ns	
Output Times											
C, $\overline{C}$ High to Output Valid	tCHQV		0.45		0.45		0.45		0.50	ns	3
C, $\overline{C}$ High to Output Hold	tCHQX	-0.45		-0.45		-0.45		-0.50		ns	3
C, $\overline{C}$ High to Echo Clock Valid	tCHCQV		0.45		0.45		0.45		0.50	ns	
C, $\overline{C}$ High to Echo Clock Hold	tCHCQX	-0.45		-0.45		-0.45		-0.50		ns	
CQ, $\overline{CQ}$ High to Output Valid	tCQHQV		0.27		0.30		0.35		0.40	ns	7
CQ, $\overline{CQ}$ High to Output Hold	tCQHQX	-0.27		-0.30		-0.35		-0.40		ns	7
$\overline{C}$, High to Output High-Z	tCHQZ		0.45		0.45		0.45		0.50	ns	3
$\overline{C}$, High to Output Low-Z	tCHQX1	-0.45		-0.45		-0.45		-0.50		ns	3
Setup Times											
Address valid to K rising edge	tAVKH	0.40		0.50		0.60		0.70		ns	
Control inputs valid to K rising edge	tIVKH	0.40		0.50		0.60		0.70		ns	2
Data-in valid to K, $\overline{K}$ rising edge	tDVKH	0.30		0.35		0.40		0.50		ns	
Hold Times											
K rising edge to address hold	tKHAX	0.40		0.50		0.60		0.70		ns	
K rising edge to control inputs hold	tKHIX	0.40		0.50		0.60		0.70		ns	
K, $\overline{K}$ rising edge to data-in hold	tKHDX	0.30		0.35		0.40		0.50		ns	

Notes: 1. All address inputs must meet the specified setup and hold times for all latching clock edges.
    2. Control singles are $\overline{R}$, $\overline{W}$, BW$_0$,BW$_1$ and BW$_2$, BW$_3$, also for x36
    3. If C,$\overline{C}$ are tied high, K,$\overline{K}$ become the references for C,$\overline{C}$ timing parameters.
    4. To avoid bus contention, at a given voltage and temperature tCHQX1 is bigger than tCHQZ.
      The specs as shown do not imply bus contention because tCHQX1 is a MIN parameter that is worst case at totally different test conditions
      (0°C, 1.9V) than tCHQZ, which is a MAX parameter(worst case at 70°C, 1.7V)
      It is not possible for two SRAMs on the same board to be at such different voltage and temperature.
    5. Clock phase jitter is the variance from clock rising edge to the next expected clock rising edge.
    6. Vdd slew rate must be less than 0.1V DC per 50 ns for DLL lock retention. DLL lock time begins once Vdd and input clock are stable.
    7. Echo clock is very tightly controlled to data valid/data hold. By design, there is a ± 0.1 ns variation from echo clock to data.
      The data sheet parameters reflect tester guardbands and test setup variations.

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THERMAL RESISTANCE

PRMETER	SYMBOL	TYP	Unit	NOTES
Junction to Ambient	θ_{JA}	21	°C/W	
Junction to Case	θ_{JC}	2.48	°C/W	

Note: Junction temperature is a function of on-chip power dissipation, package thermal impedance, mounting site temperature and mounting site thermal impedance. $T_J = T_A + P_D \times \theta_{JA}$

PIN CAPACITANCE

| PRMETER	SYMBOL	TESTCONDITION	Typ	MAX	Unit	NOTES
Address Control Input Capacitance	C_{IN}	$V_{IN}=0V$	3.5	4	pF	
Input and Output Capacitance	C_{OUT}	$V_{OUT}=0V$	4	5	pF	
Clock Capacitance	C_{CLK}	-	3	4	pF	

Note: 1. Parameters are tested with RQ=250Ω and V_{DDQ}=1.5V.

2. Periodically sampled and not 100% tested.

AC TEST CONDITIONS

Parameter	Sym-	Value	Unit
Core Power Supply Voltage	V_{DD}	1.7~1.9	V
Output Power Supply Voltage	V_{DDQ}	1.4~1.9	V
Input High/Low Level	$V_{IH}/$	1.25/0.25	V
Input Reference Level	V_{REF}	0.75	V
Input Rise/Fall Time	T_R/T_F	0.3/0.3	ns
Output Timing Reference Level		$V_{DDQ}/2$	V

Note: Parameters are tested with RQ=250Ω
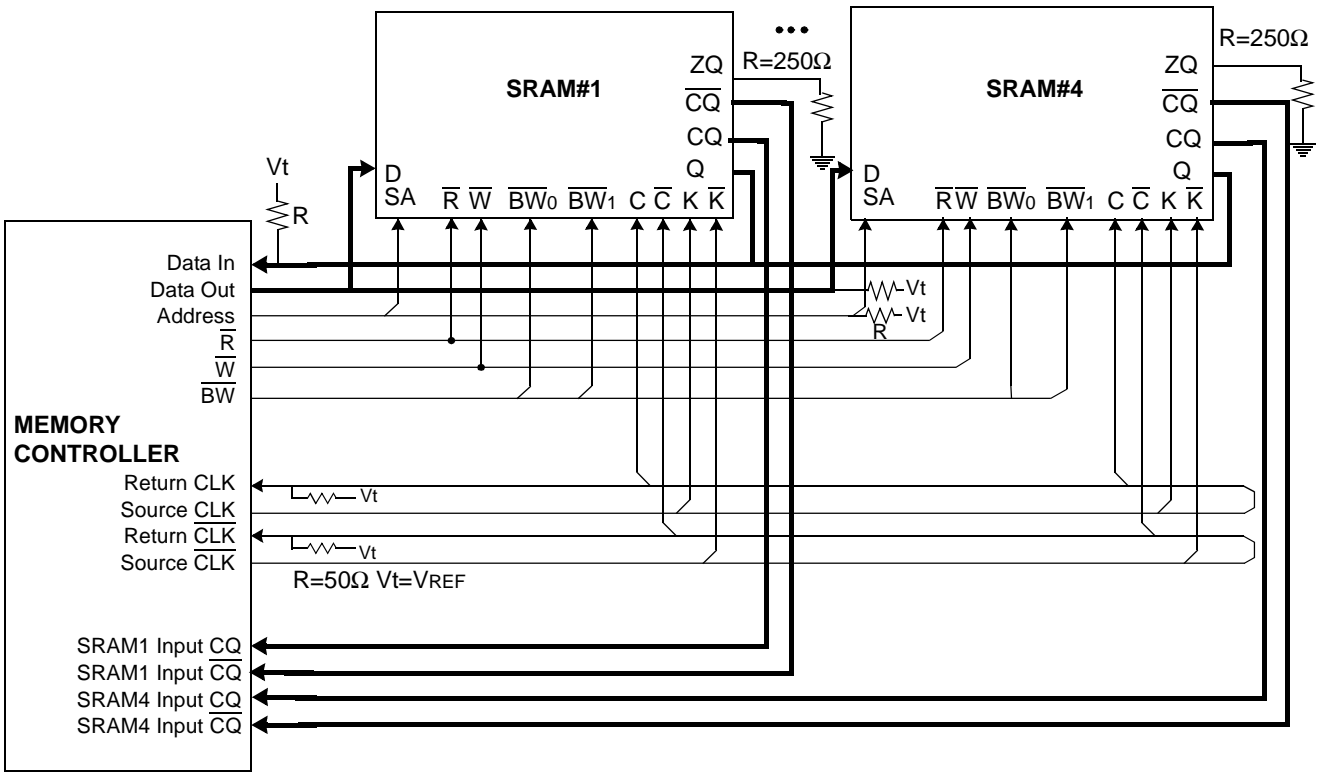
AC TEST OUTPUT LOAD

Overershoot Timing
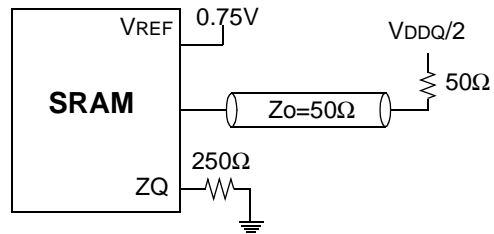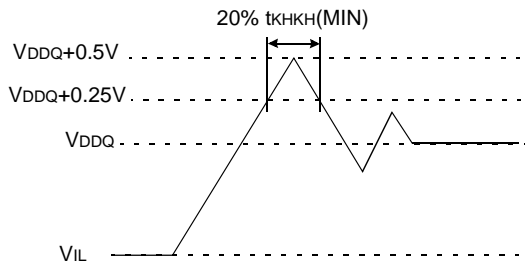
Undershoot Timing

Note: For power-up, $V_{IH} \leq V_{DDQ}+0.3V$ and $V_{DD} \leq 1.7V$ and $V_{DDQ} \leq 1.4V$ t $\leq$ 200ms
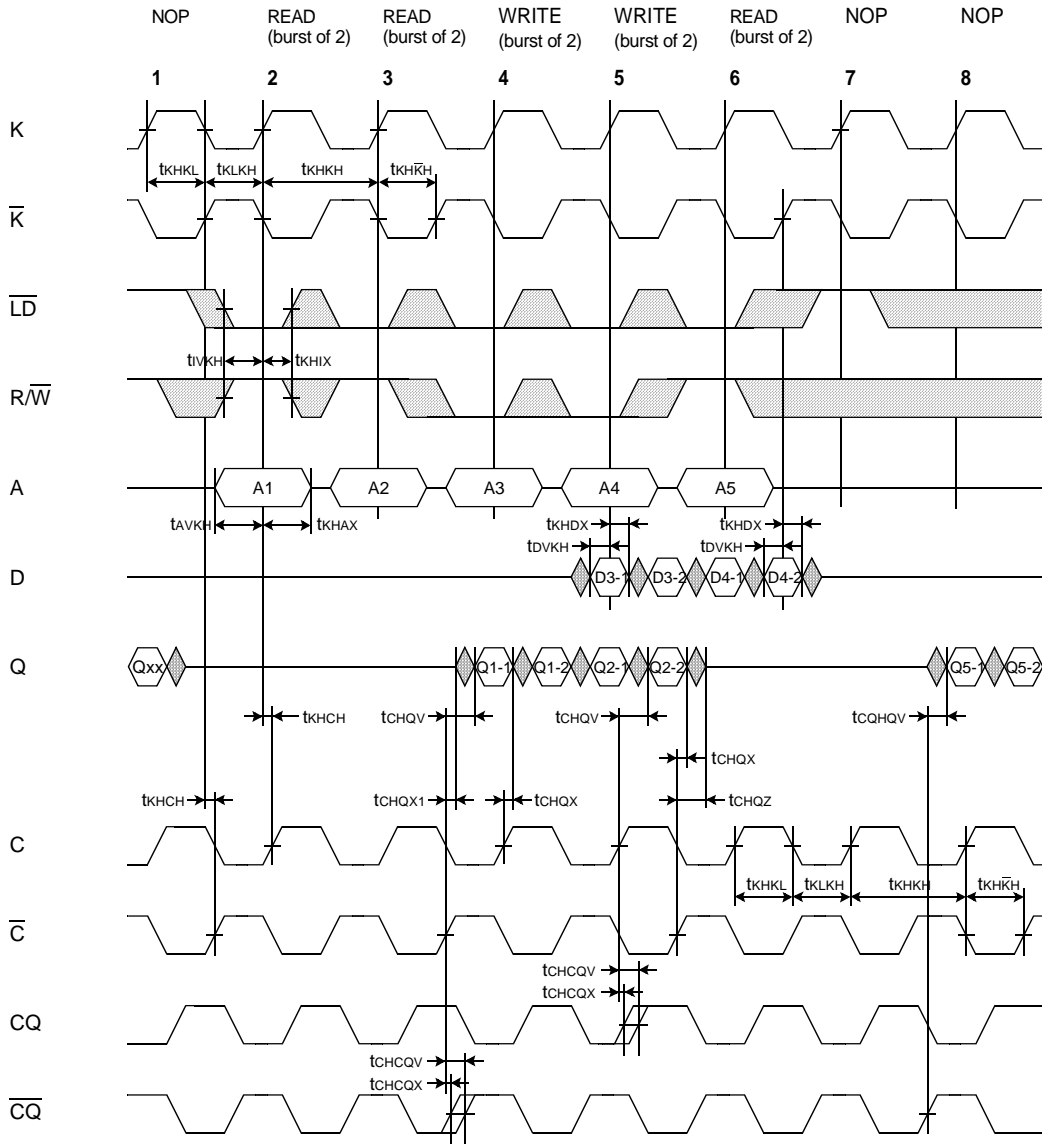
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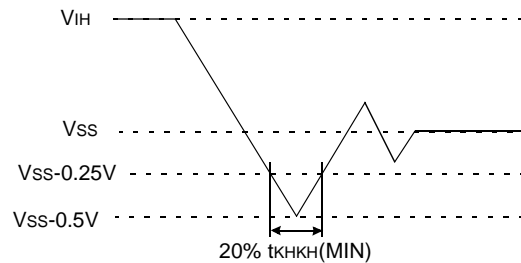
APPLICATION INRORMATION

TIMING WAVE FORMS OF READ,WRITE AND NOP

**Note**: 1. Q1-1 refers to output from address A1+0, Q1-2 refers to output from address A1+1 i.e. the next internal burst address following A1+0.

2. Outputs are disabled one cycle after a NOP.

3. D3-1 refers to input to address A3+0, D3-2 refers to input to address A3+1, i.e the next internal burst address following A3+0.

4. If address A4=A5, data Q5-1=D4-1, data Q5-2=D4-2.

Write data is forwarded immediately as read results.

IEEE 1149.1 TEST ACCESS PORT AND BOUNDARY SCAN-JTAG

This part contains an IEEE standard 1149.1 Compatible Test Access Port(TAP). The package pads are monitored by the Serial Scan circuitry when in test mode. This is to support connectivity testing during manufacturing and system diagnostics. Internal data is not driven out of the SRAM under JTAG control. In conformance with IEEE 1149.1, the SRAM contains a TAP controller, Instruction Register, Bypass Register and ID register. The TAP controller has a standard 16-state machine that resets internally upon power-up, therefore, TRST signal is not required. It is possible to use this device without utilizing the TAP. To disable the TAP controller without interfacing with normal operation of the SRAM, TCK must be tied to Vss to preclude mid level input. TMS and TDI are designed so an undriven input will produce a response identical to the application of a logic 1, and may be left unconnected. But they may also be tied to VDD through a resistor. TDO should be left unconnected.

JTAG Block Diagram
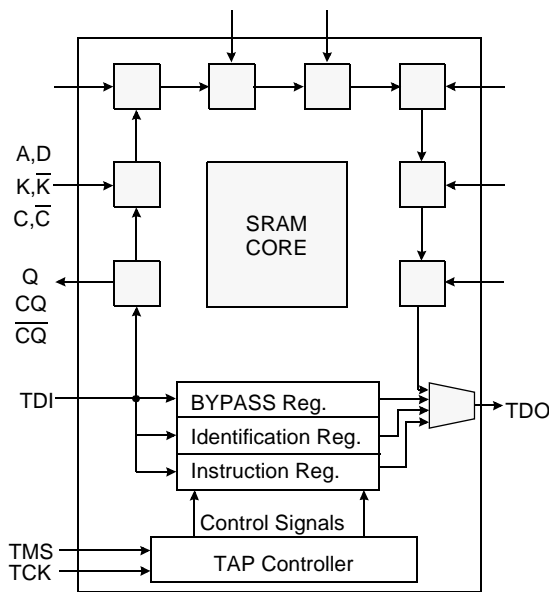
JTAG Instruction Coding

IR2	IR1	IR0	Instruction	TDO Output	Notes
0	0	0	EXTEST	Boundary Scan Register	1
0	0	1	IDCODE	Identification Register	3
0	1	0	SAMPLE-Z	Boundary Scan Register	2
0	1	1	RESERVED	Do Not Use	6
1	0	0	SAMPLE	Boundary Scan Register	5
1	0	1	RESERVED	Do Not Use	6
1	1	0	RESERVED	Do Not Use	6
1	1	1	BYPASS	Bypass Register	4

NOTE :

1. Places DQs in Hi-Z in order to sample all input data regardless of other SRAM inputs. This instruction is not IEEE 1149.1 compliant.
2. Places DQs in Hi-Z in order to sample all input data regardless of other SRAM inputs.
3. TDI is sampled as an input to the first ID register to allow for the serial shift of the external TDI data.
4. Bypass register is initiated to Vss when BYPASS instruction is invoked. The Bypass Register also holds serially loaded TDI when exiting the Shift DR states.
5. SAMPLE instruction dose not places DQs in Hi-Z.
6. This instruction is reserved for future use.

TAP Controller State Diagram

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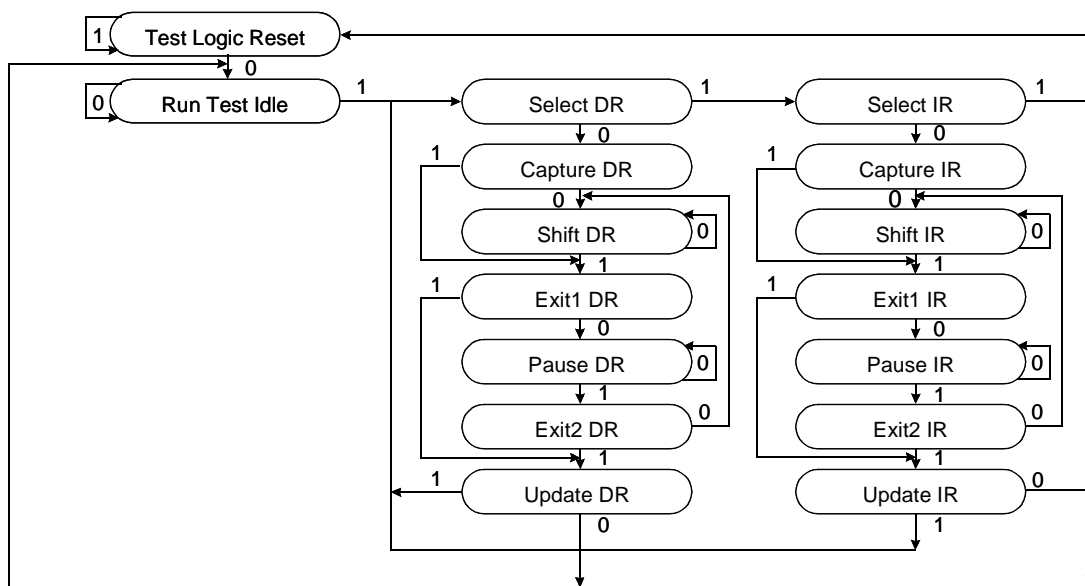
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SCAN REGISTER DEFINITION

Part	Instruction Register	Bypass Register	ID Register	Boundary Scan
2Mx36	3 bits	1 bit	32 bits	109 bits
4Mx18	3 bits	1 bit	32 bits	109 bits

ID REGISTER DEFINITION

Part	Revision Number (31:29)	Part Configuration (28:12)	Samsung JEDEC Code (11: 1)	Start Bit(0)
2Mx36	000	00def0wx0t0q0b0s0	00001001110	1
4Mx18	000	00def0wx0t0q0b0s0	00001001110	1

Note : Part Configuration

/def=011 for 72Mb, /wx=11 for x36, 10 for x18.

/t=1 for DLL Ver., 0 for non-DLL Ver. /q=1 for QDR, 0 for DDR /b=1 for 4Bit Burst, 0 for 2Bit Burst /s=1 for Separate I/O, 0 for Common I/O

BOUNDARY SCAN EXIT ORDER

ORDER	PIN ID	ORDER	PIN ID	ORDER	PIN ID
1	6R	37	10D	73	2C
2	6P	38	9E	74	3E
3	6N	39	10C	75	2D
4	7P	40	11D	76	2E
5	7N	41	9C	77	1E
6	7R	42	9D	78	2F
7	8R	43	11B	79	3F
8	8P	44	11C	80	1G
9	9R	45	9B	81	1F
10	11P	46	10B	82	3G
11	10P	47	11A	83	2G
12	10N	48	10A	84	1H
13	9P	49	9A	85	1J
14	10M	50	8B	86	2J
15	11N	51	7C	87	3K
16	9M	52	6C	88	3J
17	9N	53	8A	89	2K
18	11L	54	7A	90	1K
19	11M	55	7B	91	2L
20	9L	56	6B	92	3L
21	10L	57	6A	93	1M
22	11K	58	5B	94	1L
23	10K	59	5A	95	3N
24	9J	60	4A	96	3M
25	9K	61	5C	97	1N
26	10J	62	4B	98	2M
27	11J	63	3A	99	3P
28	11H	64	2A	100	2N
29	10G	65	1A	101	2P
30	9G	66	2B	102	1P
31	11F	67	3B	103	3R
32	11G	68	1C	104	4R
33	9F	69	1B	105	4P
34	10F	70	3D	106	5P
35	11E	71	3C	107	5N
36	10E	72	1D	108	5R
				109	Internal

Note: 1. NC pins are read as "X" (i.e. don't care.)

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JTAG DC OPERATING CONDITIONS

Parameter	Symbol	Min	Typ	Max	Unit	Note
Power Supply Voltage	V_{DD}	1.7	1.8	1.9	V	
Input High Level	V_{IH}	1.3	-	$V_{DD}+0.3$	V	
Input Low Level	V_{IL}	-0.3	-	0.5	V	
Output High Voltage(I_{OH}=-2mA)	V_{OH}	1.4	-	V_{DD}	V	
Output Low Voltage(I_{OL}=2mA)	V_{OL}	V_{SS}	-	0.4	V	

Note: 1. The input level of SRAM pin is to follow the SRAM DC specification.

JTAG AC TEST CONDITIONS

Parameter	Symbol	Min	Unit	Note
Input High/Low Level	V_{IH}/V_{IL}	1.3/0.5	V	
Input Rise/Fall Time	TR/TF	1.0/1.0	ns	
Input and Output Timing Reference Level		0.9	V	1

Note: 1. See SRAM AC test output load on page 11.

JTAG AC Characteristics

Parameter	Symbol	Min	Max	Unit	Note
TCK Cycle Time	t_{CHCH}	50	-	ns	
TCK High Pulse Width	t_{CHCL}	20	-	ns	
TCK Low Pulse Width	t_{CLCH}	20	-	ns	
TMS Input Setup Time	t_{MVCH}	5	-	ns	
TMS Input Hold Time	t_{CHMX}	5	-	ns	
TDI Input Setup Time	t_{DVCH}	5	-	ns	
TDI Input Hold Time	t_{CHDX}	5	-	ns	
SRAM Input Setup Time	t_{SVCH}	5	-	ns	
SRAM Input Hold Time	t_{CHSX}	5	-	ns	
Clock Low to Output Valid	t_{CLQV}	0	10	ns	

JTAG TIMING DIAGRAM

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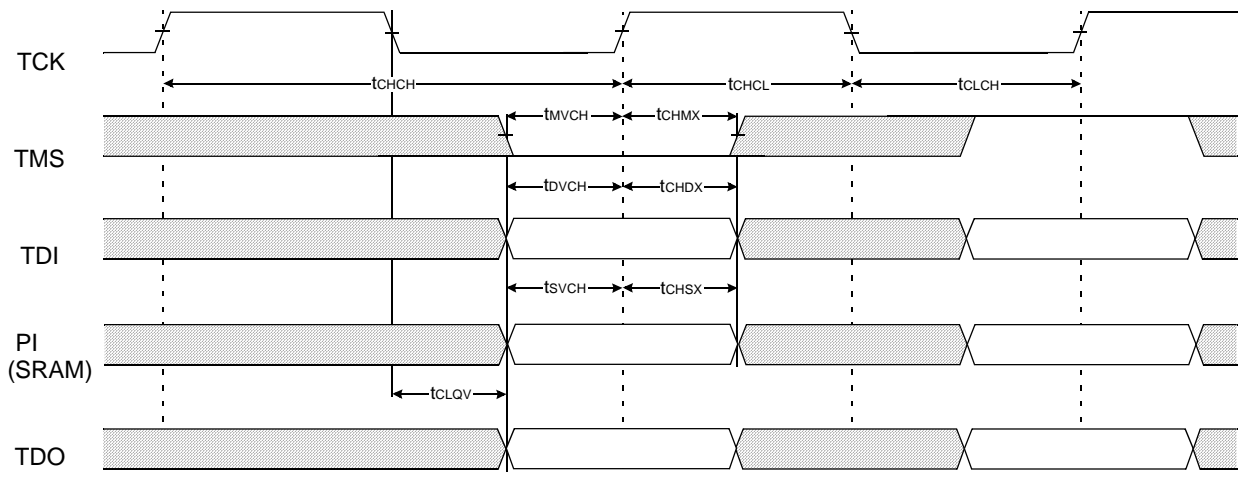
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165 FBGA PACKAGE DIMENSIONS

15mm x 17mm Body, 1.0mm Bump Pitch, 11x15 Ball Array
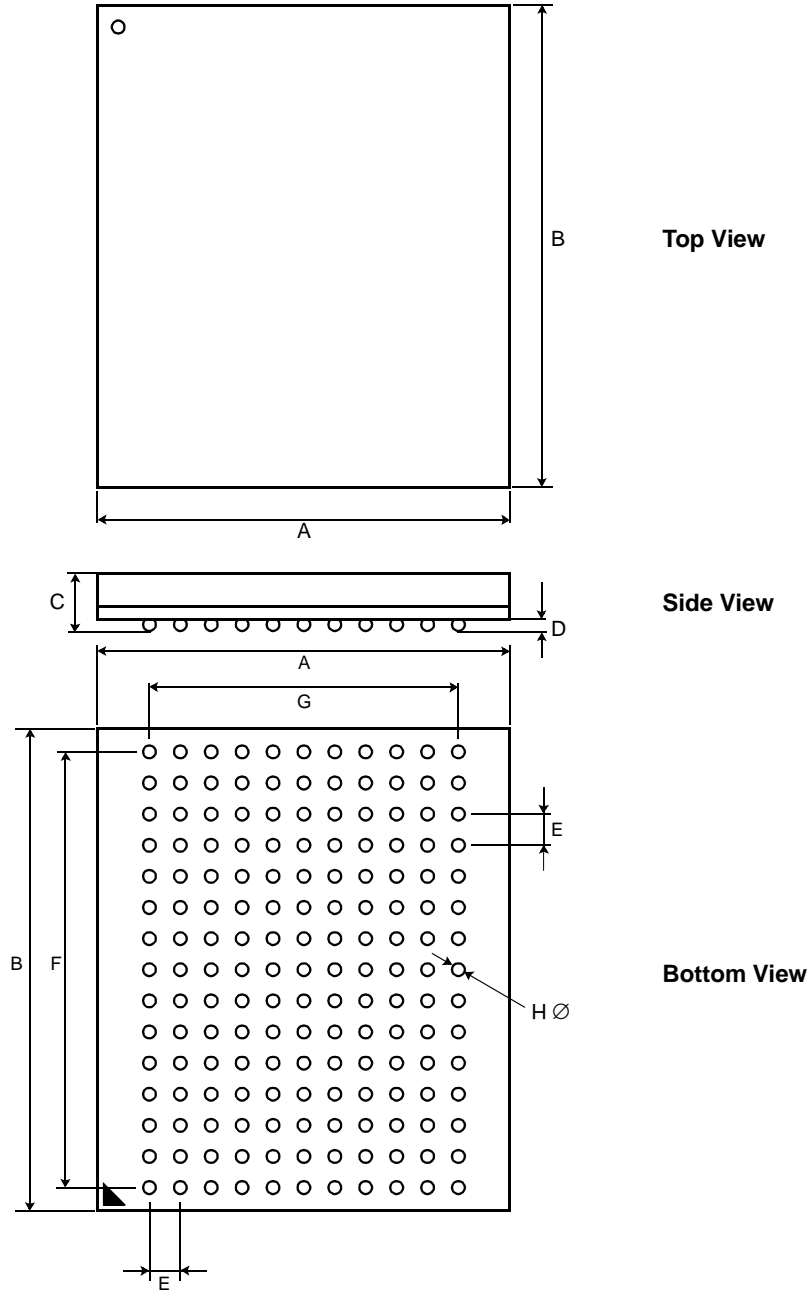
Symbol	Value	Units	Note	Symbol	Value	Units	Note
A	15 ± 0.1	mm		**E**	1.0	mm	
B	17 ± 0.1	mm		**F**	14.0	mm	
C	1.3 ± 0.1	mm		**G**	10.0	mm	
D	0.35 ± 0.05	mm		**H**	0.5 ± 0.05	mm	

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